

TVS Diode

Transient Voltage Suppressor Diodes

ESD206-B1-02V

Ultra Low Clamping Bi-directional ESD / Transient / Surge Protection Diode

ESD206-B1-02V

Data Sheet

Revision 1.2, 2013-12-19
Final

Revision History: Rev. 1.1, 2013-11-26

| Page or Item | Subjects (major changes since previous revision) |
|---------------------------------|--|
| Revision 1.2, 2013-12-19 | |
| 5 | Update Table 2-2) |
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Last Trademarks Update 2010-10-26

1 Ultra Low Clamping Bi-directional ESD / Transient / Surge Protection Diode

1.1 Features

- ESD/Transient/Surge protection of one data / V_{bus} line exceeding standard:
 - IEC61000-4-2 (ESD): ± 30 kV (air/contact discharge)
 - IEC61000-4-4 (EFT): ± 50 A (5/50 ns)
 - IEC61000-4-5 (surge): ± 6 A (8/20 μ s)
- Medium capacitance: $C_L = 12$ pF (typ.)
- Bi-directional symmetrical working voltage: -5.5 V to $+5.5$ V
- Low leakage current
- Very low ESD clamping voltage: 9 V (typ.)
- Very low dynamic resistance: 0.15Ω (typ.)
- Pb-free (RoHS compliant) and halogen free package



1.2 Application Examples

- Audio Line, Speaker, Headset, Microphone Protection
- Human Interface Devices (Keyboard, Touchpad, Buttons)

1.3 Product Description

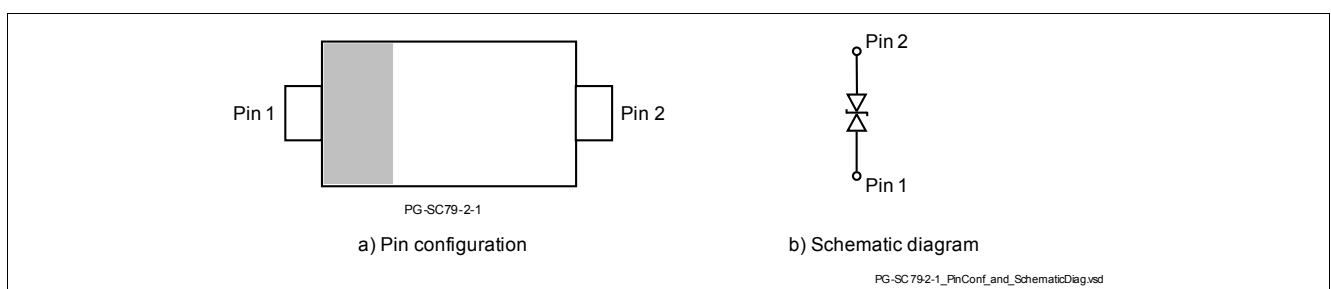


Figure 1-1 Pin Configuration and Schematic Diagram

Table 1-1 Ordering Information

| Type | Package | Configuration | Marking code |
|---------------|---------|------------------------|--------------|
| ESD206-B1-02V | SC79 | 1 line, bi-directional | e |

2 Characteristics

2.1 Maximum Ratings

Table 2-1 Maximum Ratings at $T_A = 25\text{ °C}$, unless otherwise specified¹⁾

| Parameter | Symbol | Values | | | Unit |
|--|-----------|--------|------|------|------|
| | | Min. | Typ. | Max. | |
| ESD ²⁾ air / contact discharge | V_{ESD} | - | - | 30 | kV |
| Peak pulse current ($t_p = 8/20\ \mu\text{s}$) ³⁾ | I_{PP} | - | - | 6 | A |
| Operating temperature range | T_{OP} | -55 | - | 125 | °C |
| Storage temperature | T_{stg} | -65 | - | 150 | °C |

- 1) Device is electrically symmetrical
- 2) V_{ESD} according to IEC61000-4-2
- 3) I_{PP} according to IEC61000-4-5

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

2.2 Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

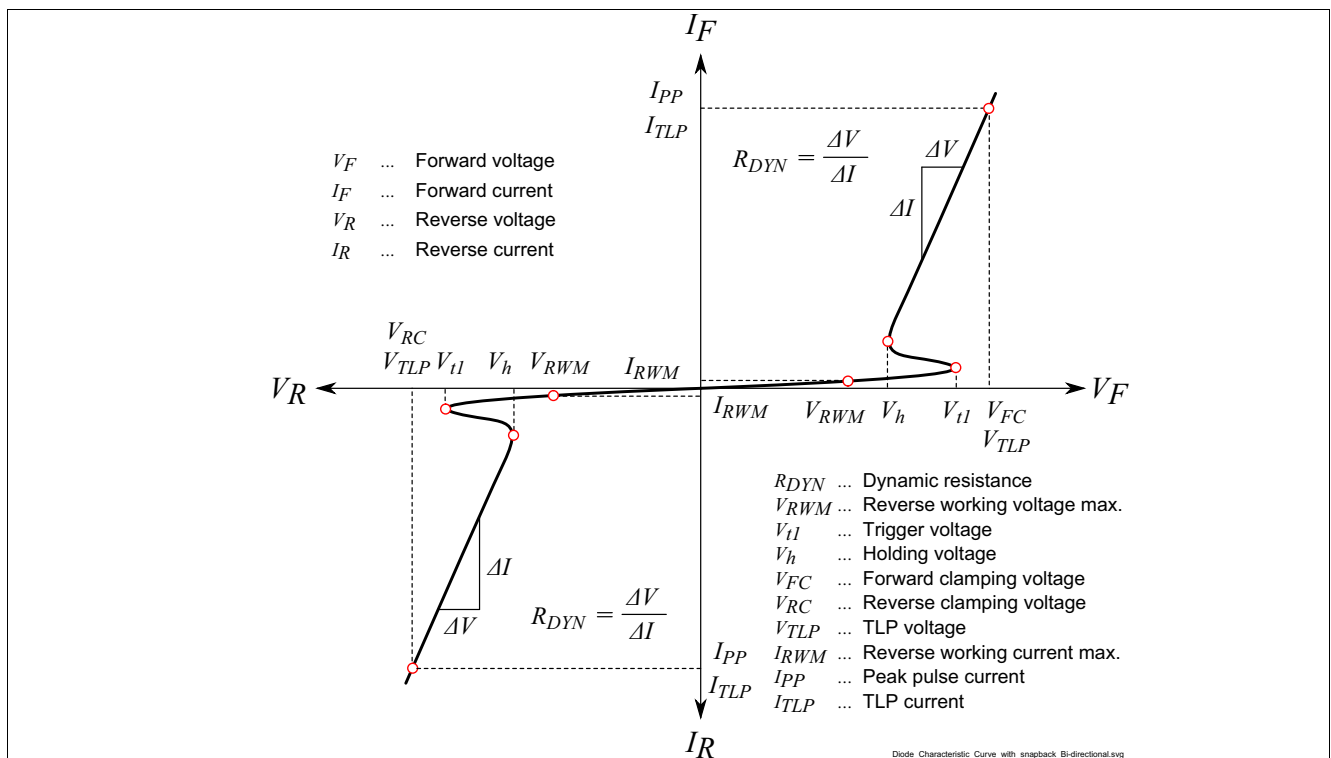


Figure 2-1 Definitions of electrical characteristics

Table 2-2 DC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified¹⁾

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------|-----------|--------|------|------|------|-----------------------|
| | | Min. | Typ. | Max. | | |
| Reverse working voltage | V_{RWM} | - | - | 5.5 | V | |
| Reverse current | I_R | - | - | 50 | nA | $V_R = 5.5\text{ V}$ |
| Trigger voltage | V_{t1} | 6.1 | - | - | V | |
| Holding voltage | V_h | 6.1 | 8 | 9.5 | V | $I_R = 10\text{ mA}$ |

1) Device is electrically symmetrical

Table 2-3 AC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|------------------|--------|--------|------|------|------|--------------------------------------|
| | | Min. | Typ. | Max. | | |
| Line capacitance | C_L | - | 12 | 20 | pF | $V_R = 0\text{ V}, f = 1\text{ MHz}$ |

Table 2-4 ESD and Surge Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|-----------|--------|------|------|----------|-------------------------|
| | | Min. | Typ. | Max. | | |
| Clamping voltage ¹⁾ | V_{CL} | - | 8 | - | V | $I_{TLP} = 16\text{ A}$ |
| | | - | 11.5 | - | | $I_{TLP} = 30\text{ A}$ |
| Clamping voltage ²⁾ | | - | 8 | - | | $I_{PP} = 1\text{ A}$ |
| | | - | 10 | - | | $I_{PP} = 6\text{ A}$ |
| Dynamic resistance ¹⁾ | R_{DYN} | - | 0.15 | - | Ω | |

1) ANSI/ESD STM5.5.1 - Electrostatic Discharge Sensitive Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 0.6\text{ ns}$, I_{TLP} and V_{TLP} averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristic between $I_{TLP1} = 10\text{ A}$ and $I_{TLP2} = 40\text{ A}$. Please refer to Application Note AN210[1].

2) I_{PP} according to IEC61000-4-5 ($t_p = 8/20\ \mu\text{s}$)

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

3 Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

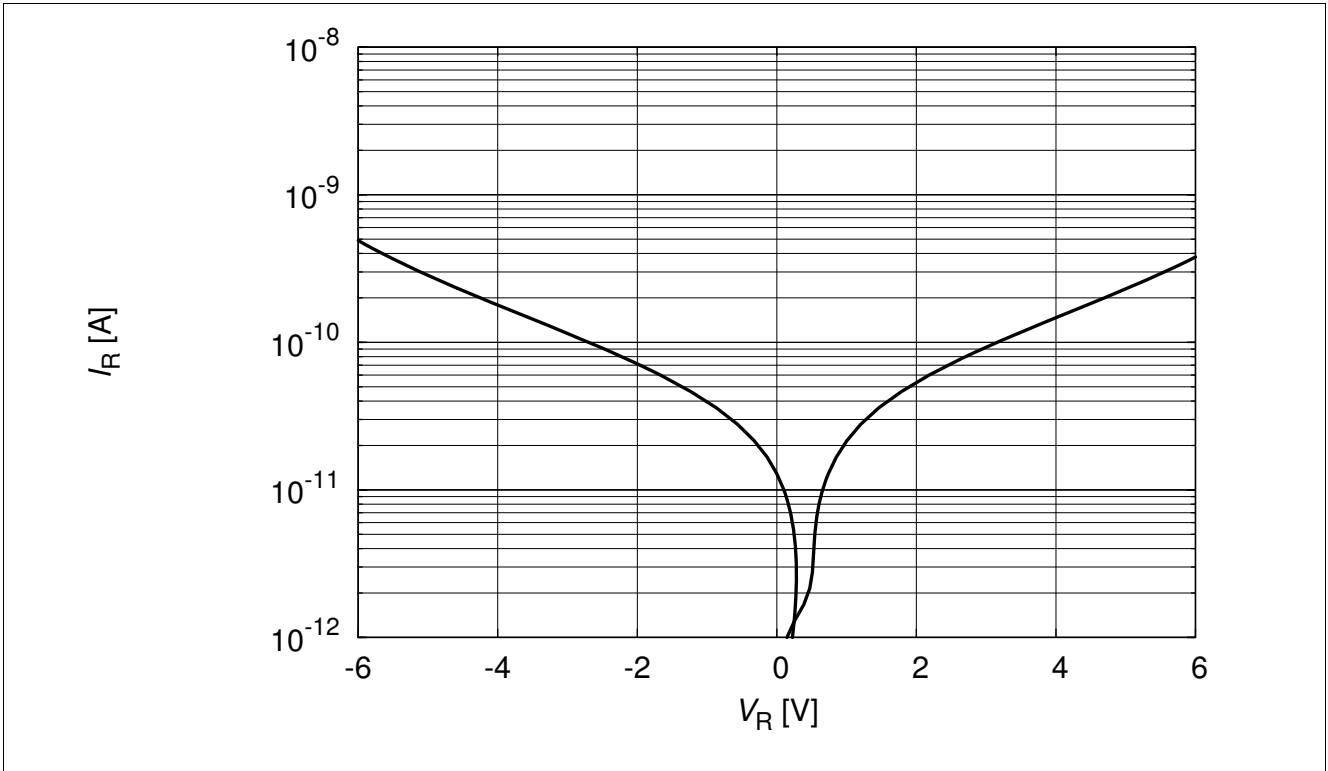


Figure 3-1 Reverse current, $I_R = f(V_R)$

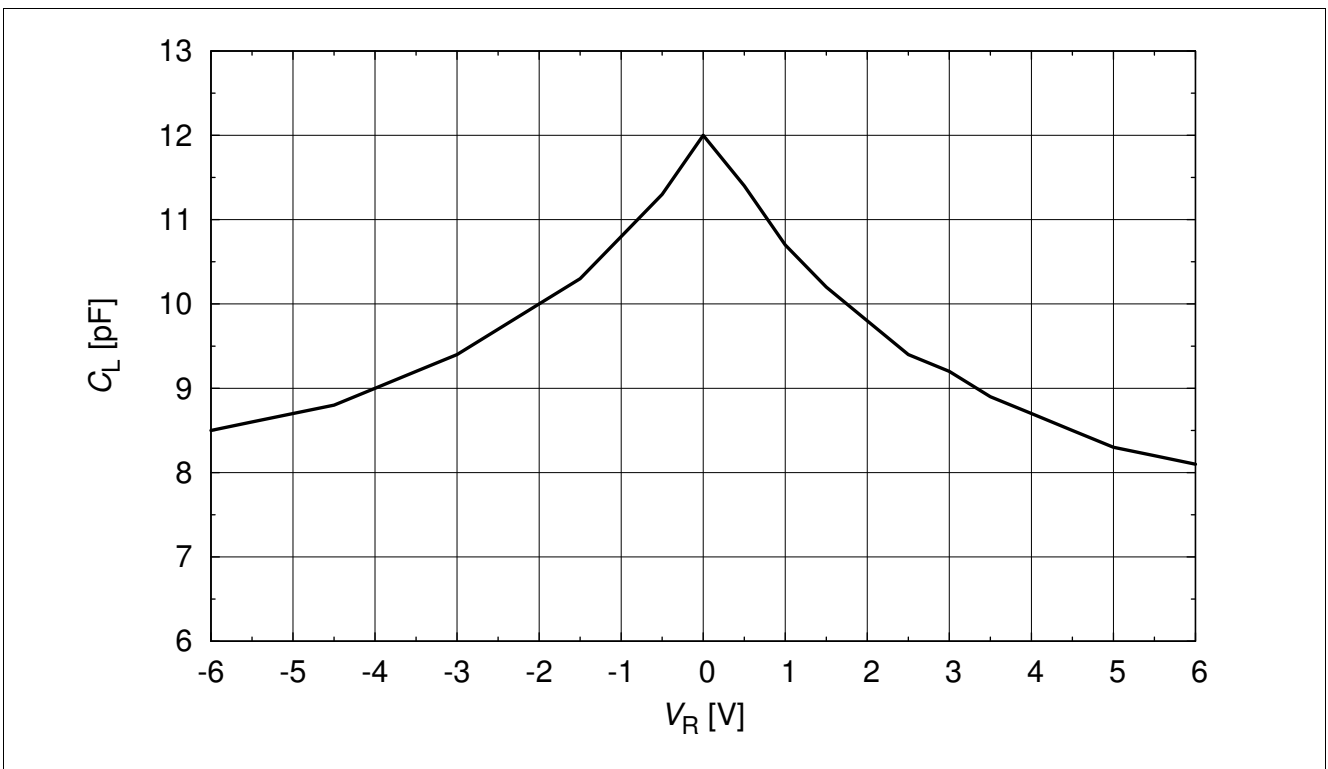


Figure 3-2 Line capacitance: $C_L = f(V_R), f = 1\text{ MHz}$

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

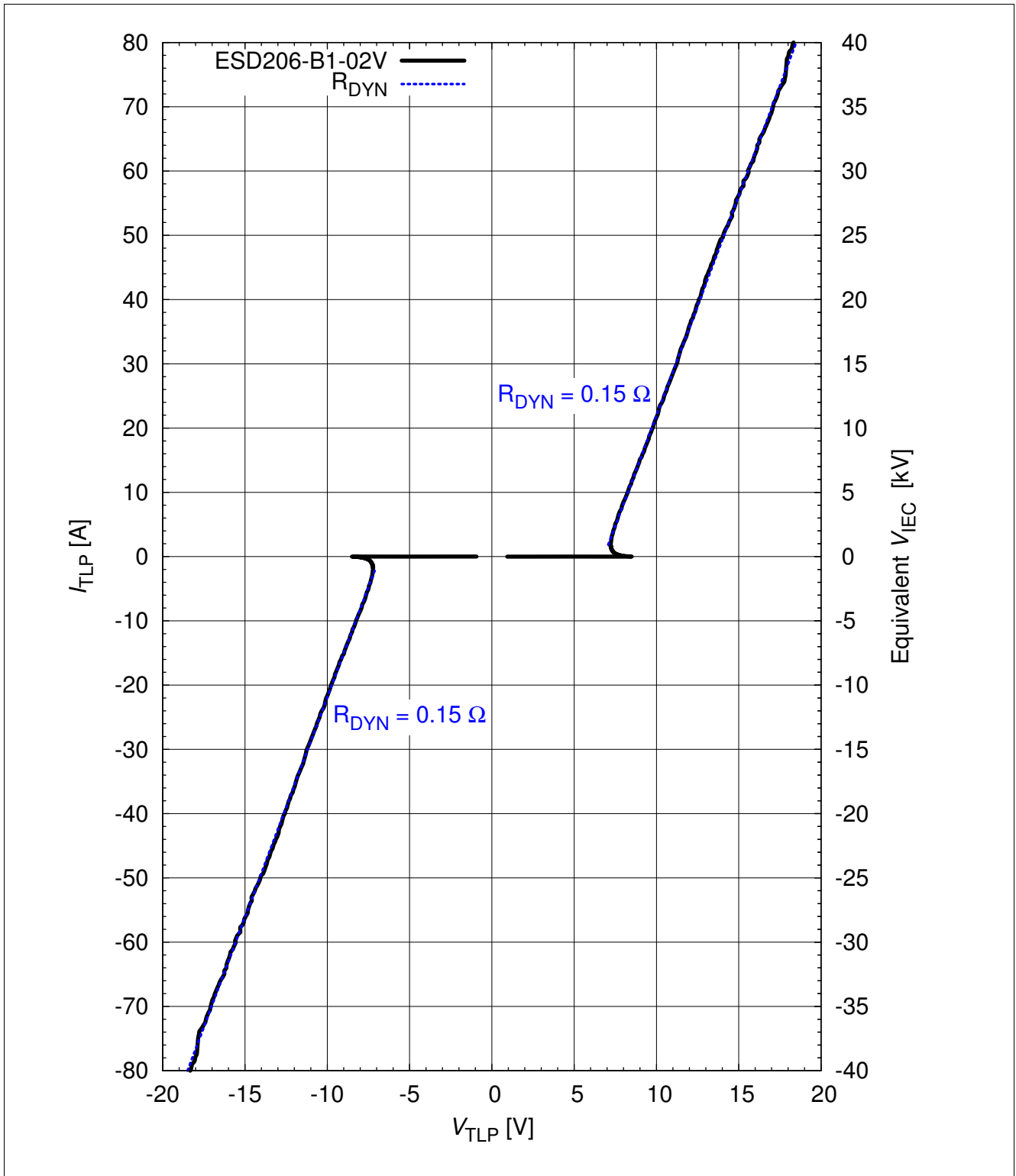


Figure 3-3 Clamping voltage $V_{TLP} = f(I_{TLP})$ [1]

Note: TLP parameter: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristic between $I_{TLP1} = 10\text{ A}$ and $I_{TLP2} = 40\text{ A}$. The equivalent stress level V_{IEC} according IEC 61000-4-2 ($R = 330\ \Omega$, $C = 150\text{ pF}$) is calculated at the broad peak of the IEC waveform at $t = 30\text{ ns}$ with 2 A/kV

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

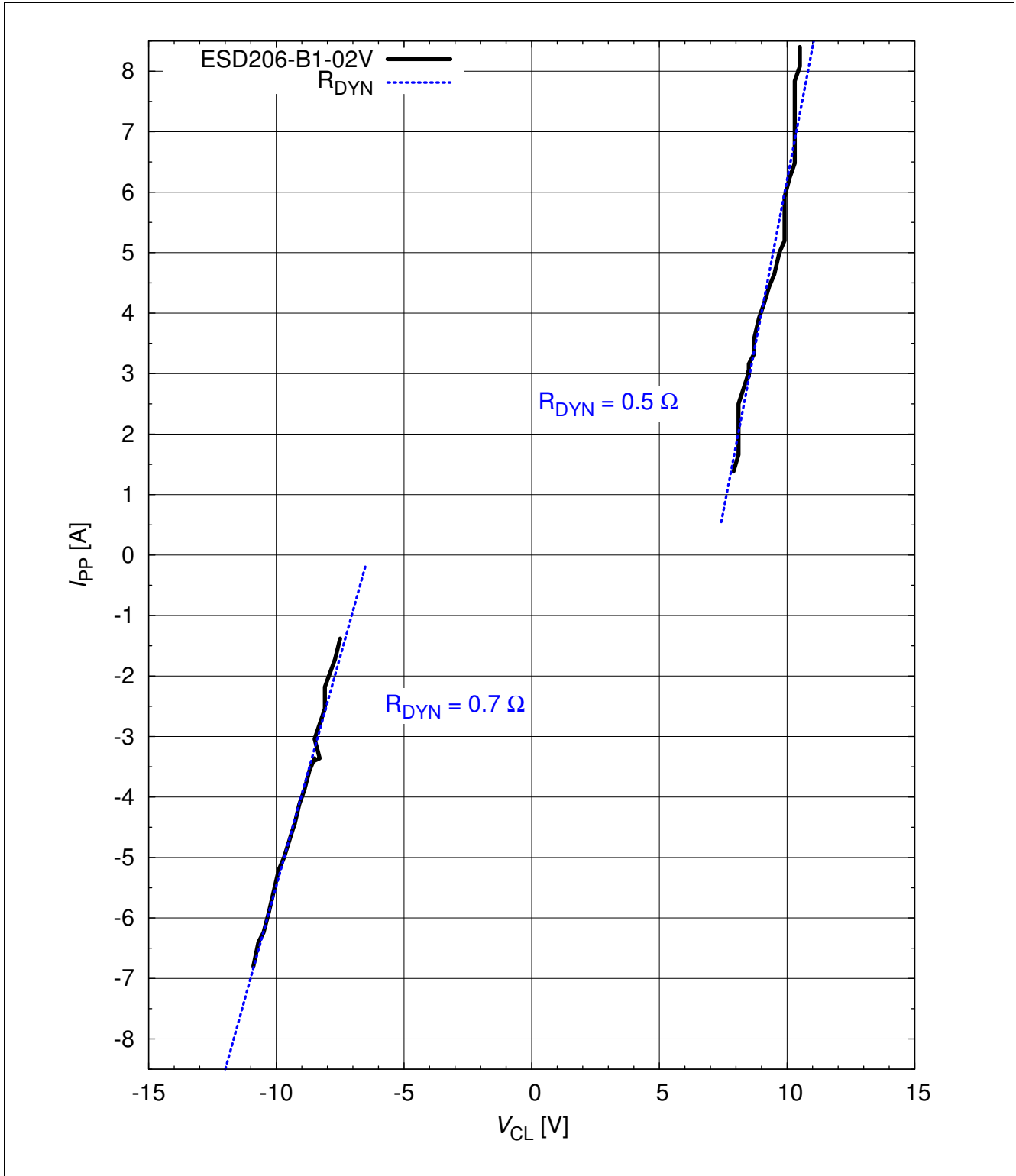


Figure 3-4 Pulse current (IEC61000-4-5) versus clamping voltage: $I_{PP} = f(V_{CL})$

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

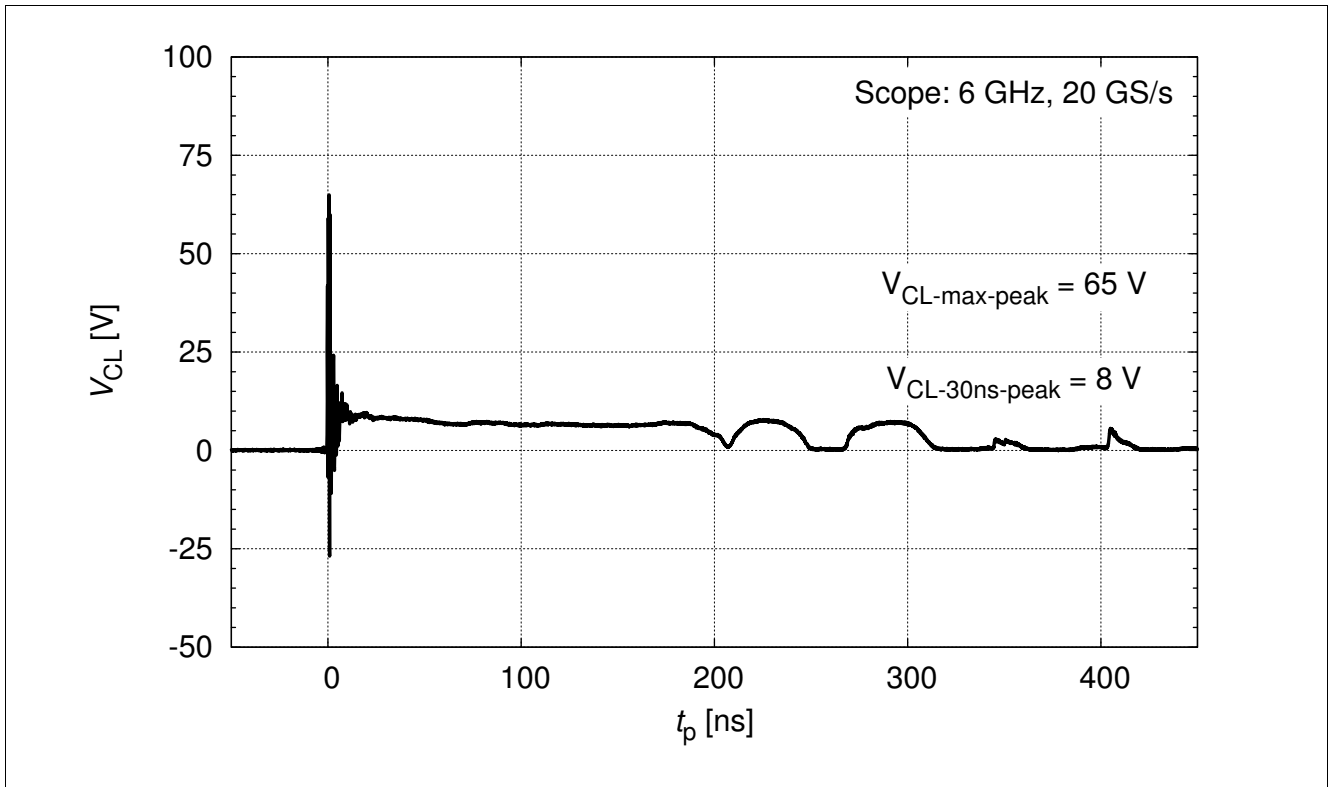


Figure 3-5 Clamping voltage at +8 kV discharge according IEC61000-4-2 ($R = 330\ \Omega$, $C = 150\ \text{pF}$)

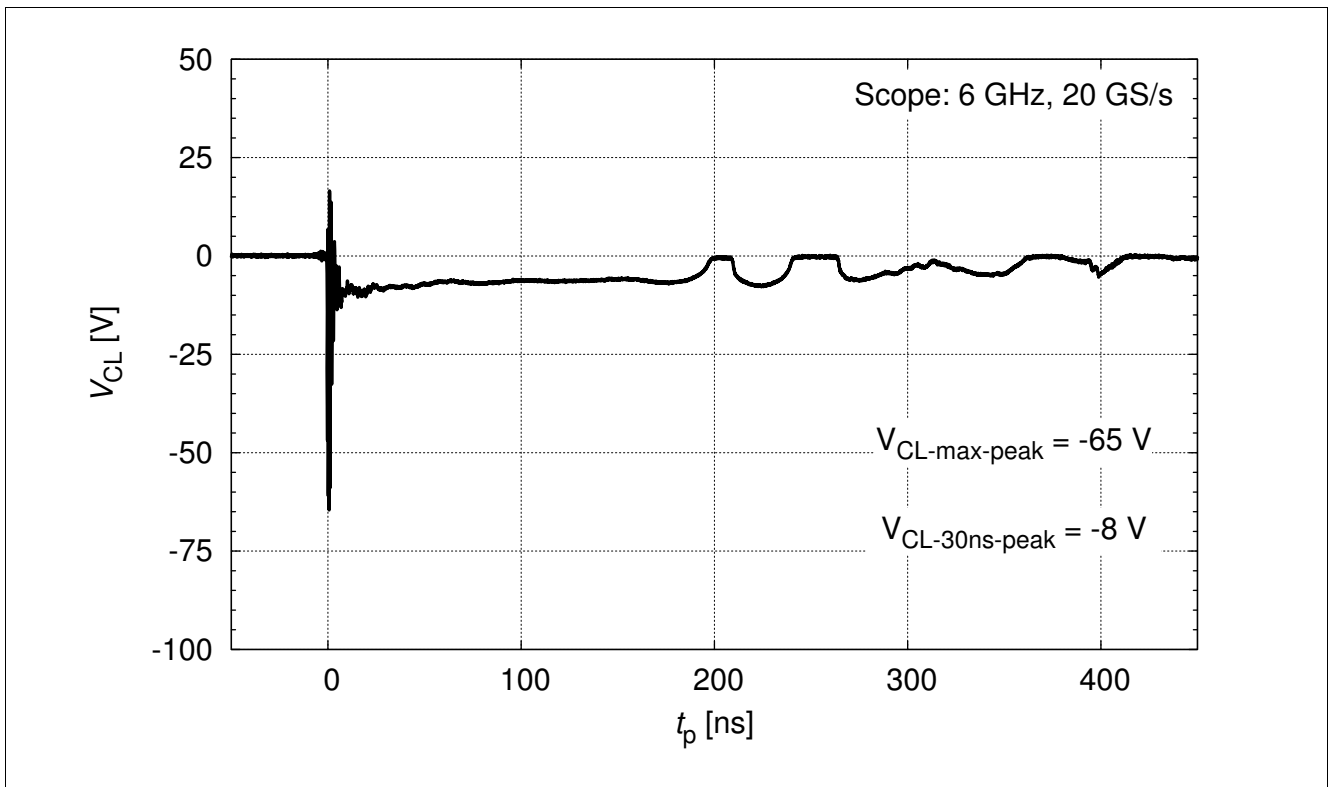


Figure 3-6 Clamping voltage at -8 kV discharge according IEC61000-4-2 ($R = 330\ \Omega$, $C = 150\ \text{pF}$)

Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

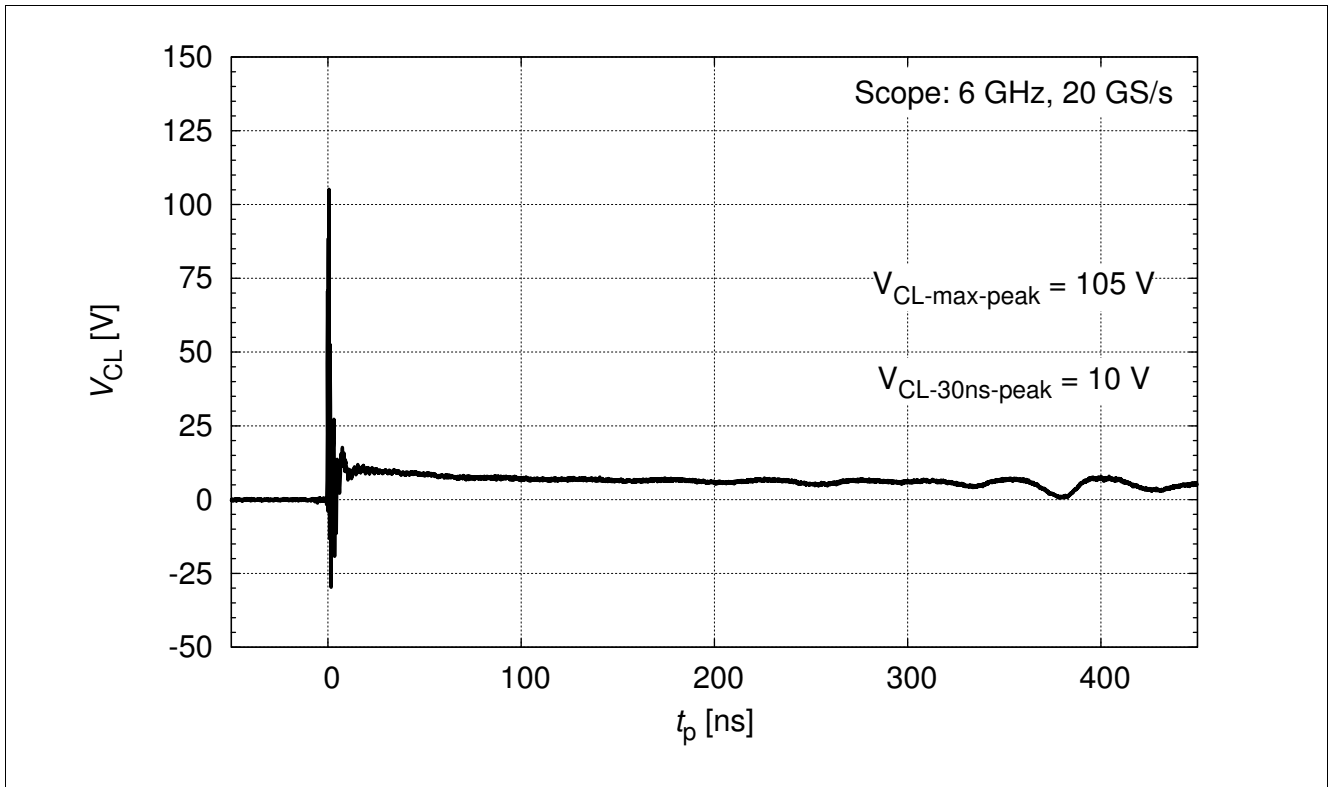


Figure 3-7 Clamping voltage at +15 kV discharge according IEC61000-4-2 ($R = 330\text{ Ohm}$, $C = 150\text{ pF}$)

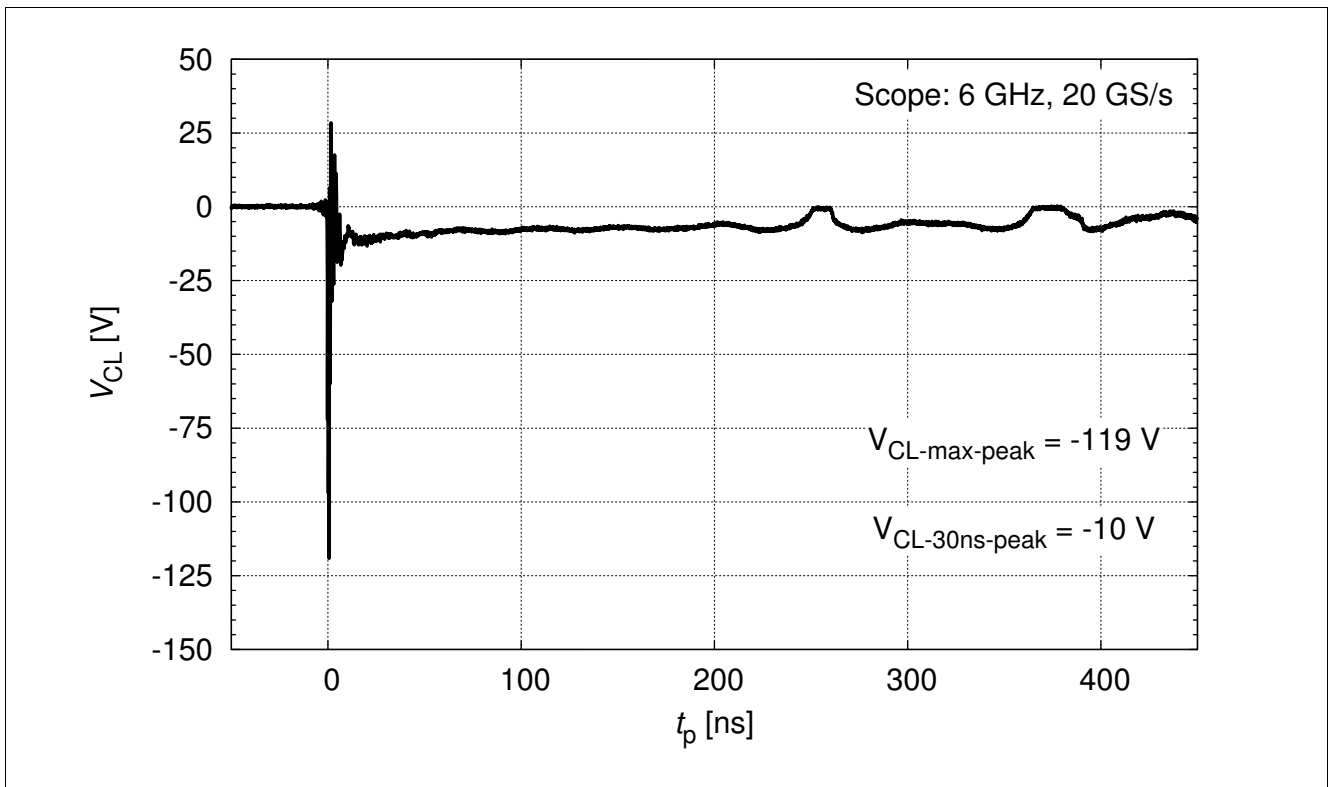


Figure 3-8 Clamping voltage at -15 kV discharge according IEC61000-4-2 ($R = 330\text{ }\Omega$, $C = 150\text{ pF}$)

4 Package Information

4.1 SC79

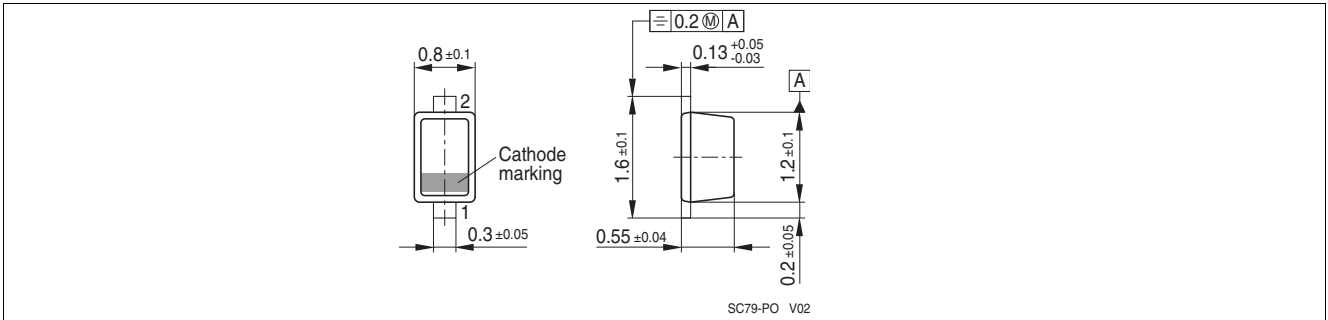


Figure 4-1 SC79: Package outline(dimension in mm)

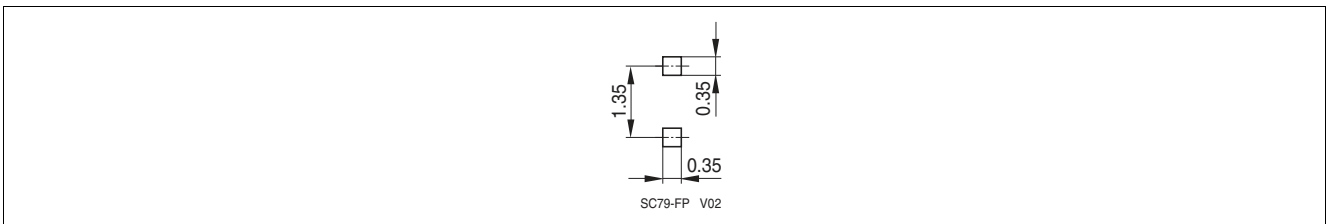


Figure 4-2 SC79: Footprint (dimension in mm)

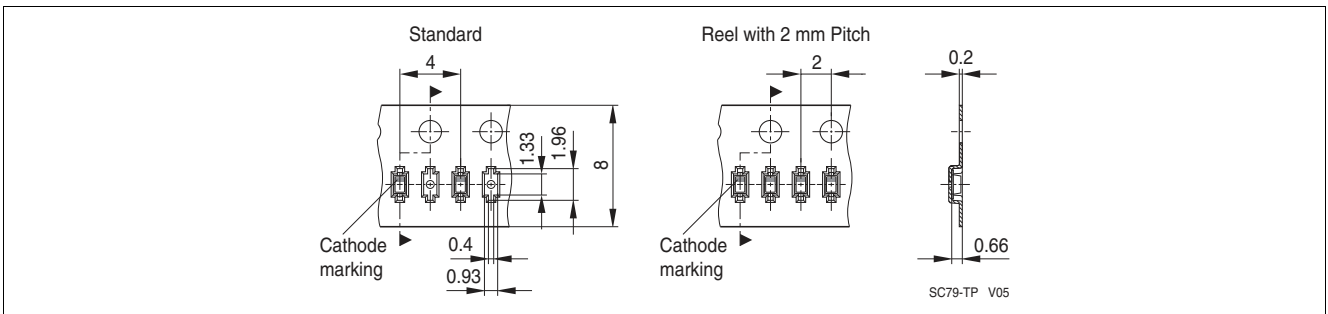


Figure 4-3 SC79: Tape and reel (dimension in mm)

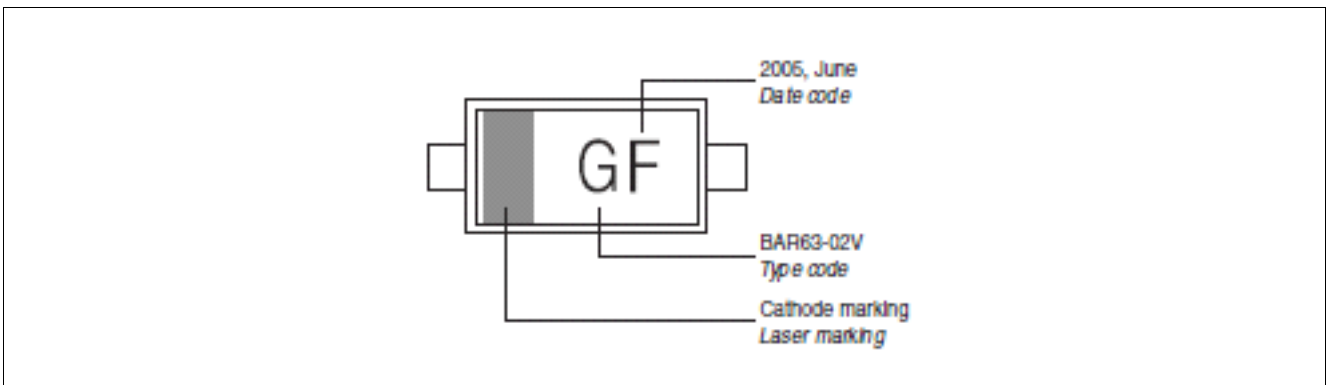


Figure 4-4 SC79: Marking example

References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology

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